

N-Channel Enhancement Mode Power MOSFET

Description

The FNK2012E uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 1.8V. This device is suitable for use as a load switch or in PWM applications .It is ESD protested.

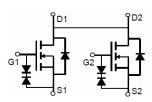
General Features

• $V_{DS} = 20V, I_D = 8A$ $R_{DS(ON)} < 17m\Omega @ V_{GS} = 2.5V$ $R_{DS(ON)} < 13m\Omega @ V_{GS} = 4.5V$ ESD Rating: 2000V HBM

- High power and current handing capability
- Lead free product is acquired
- Surface mount package

Application

- Uni-directional load switch
- Bi-directional load switch



Schematic diagram



Marking and pin Assignment



TSSOP-8 top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
FNK2012E	FNK2012E	TSSOP-8	Ø330mm	12mm	3000 units

Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	Vds	20	V
Gate-Source Voltage	Vgs	±12	V
Drain Current-Continuous	I _D	8	A
Drain Current-Pulsed (Note 1)	I _{DM}	30	A
Maximum Power Dissipation	PD	2	W
Operating Junction and Storage Temperature Range	TJ,TSTG	-55 To 150	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)R _{0JA} 62.5°C/W

Electrical Characteristics (T_A=25 $^{\circ}$ C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	20			V
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} =20V, V_{GS} =0V	-	-	1	μA



Parameter	Symbol	Condition	Min	Тур	Max	Unit
Gate-Body Leakage Current	I _{GSS}	V_{GS} =±10V, V_{DS} =0V	-	-	±10	μA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	0.45	0.7	1.0	V
Drain-Source On-State Resistance	R _{DS(ON)}	V_{GS} =4.5V, I_D =8A	-	11	13	mΩ
		V_{GS} =2.5V, I _D =6.5A	-	12.8	17	mΩ
Forward Transconductance	g fs	V _{DS} =5V,I _D =5A	_	15	-	S
Dynamic Characteristics (Note4)			•			
Input Capacitance	C _{lss}		-	1100	-	PF
Output Capacitance	C _{oss}		-	230	-	PF
Reverse Transfer Capacitance	C _{rss}		-	200	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	2.5		nS
Turn-on Rise Time	tr		-	7.2		nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10V, R_{GEN} =3 Ω	-	49		nS
Turn-Off Fall Time	t _f		-	10.8		nS
Total Gate Charge	Qg		-	17.9		nC
Gate-Source Charge	Q _{gs}	50 , 5 ,	-	1.5	-	nC
Gate-Drain Charge	Q _{gd}	V _{GS} =4.5V	-	4.7	-	nC
Drain-Source Diode Characteristics			·			•
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =8A	-	-	1.2	V
Diode Forward Current (Note 2)	I _S		-	-	8	А

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, $t \le 10$ sec.

3. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

4. Guaranteed by design, not subject to production



Typical Electrical and Thermal Characteristics

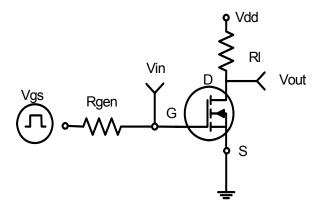
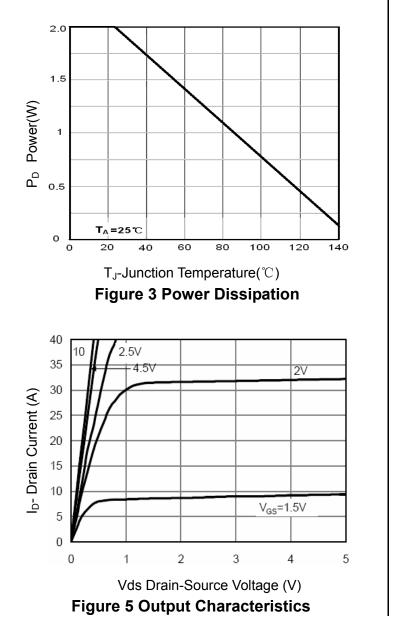
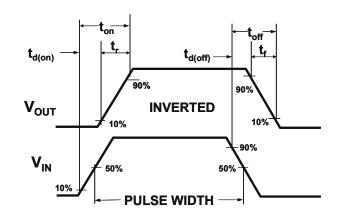


Figure 1:Switching Test Circuit







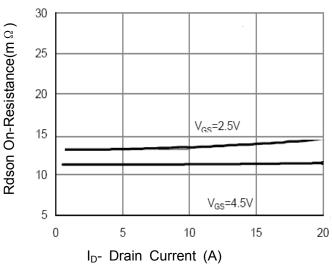
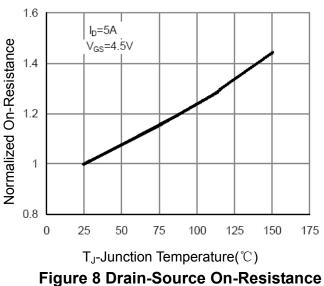
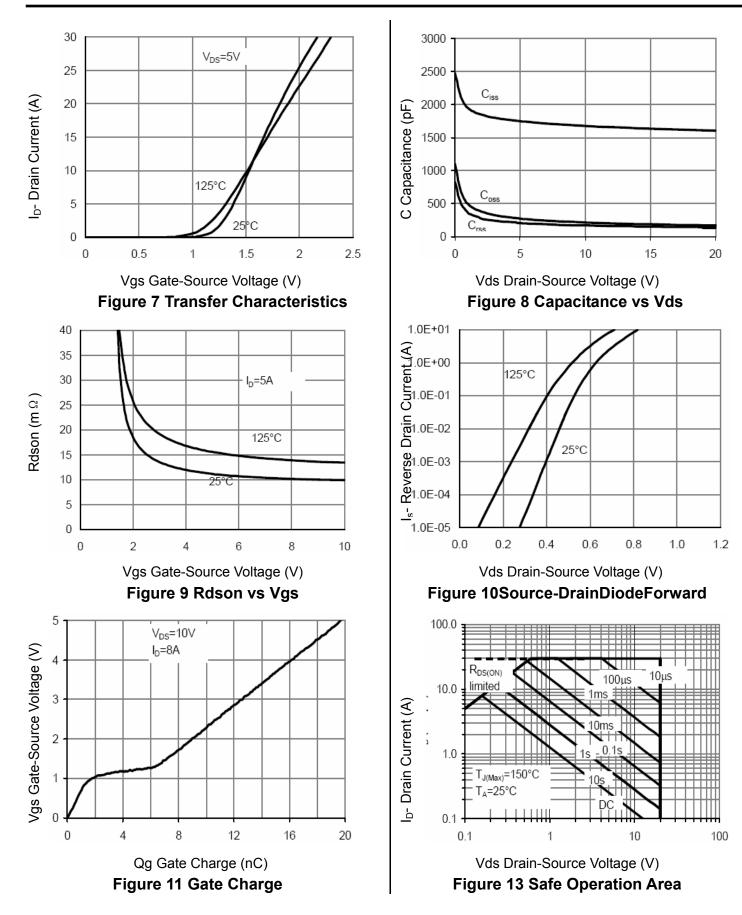


Figure 6 Drain-Source On-Resistance









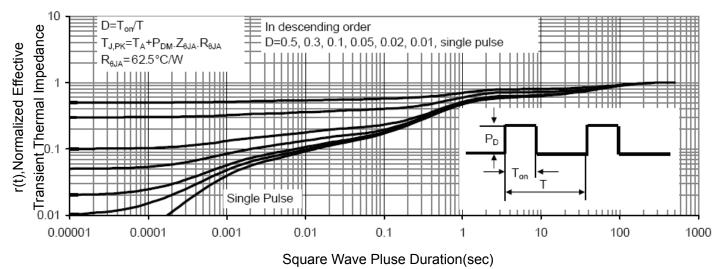
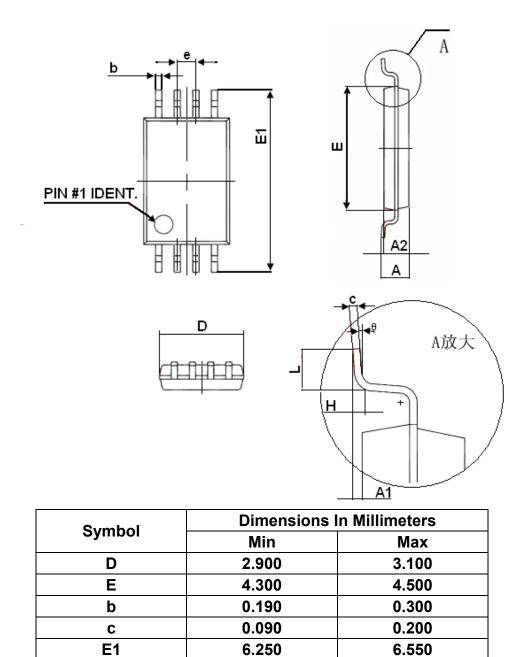


Figure 14 Normalized Maximum Transient Thermal Impedance



Tssop-8 Package Information



A2	0.800	
A1	0.020	
е	0.65	(BSC)
L	0.500	
Н	0.25	(TYP)
Θ	1°	

Α

1.100

1.000 0.150

0.700

7°



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